WR0<5 ĮMĮ Ь QSQ ÆḾ ч s ‖ ㄱ Silicon NPN transistor in a TO-92 Plastic Package.

ت ⊐ я ∪ Ң ı Э ╙ ш ` ≠ ό Ḅ ı ль 5VD48 ; 8 Й ´
Low $V_{CE(sat)}$,excellent current gain characteristics complementary pair with 2SA1585.

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Low frequency amplifier.

PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

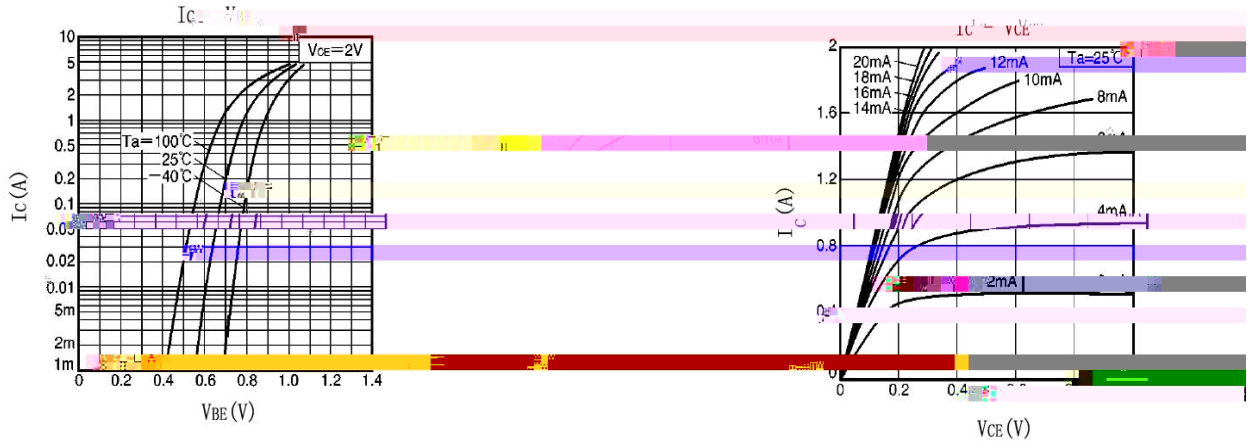
/ Absolute Maximum Ratings(Ta=25)

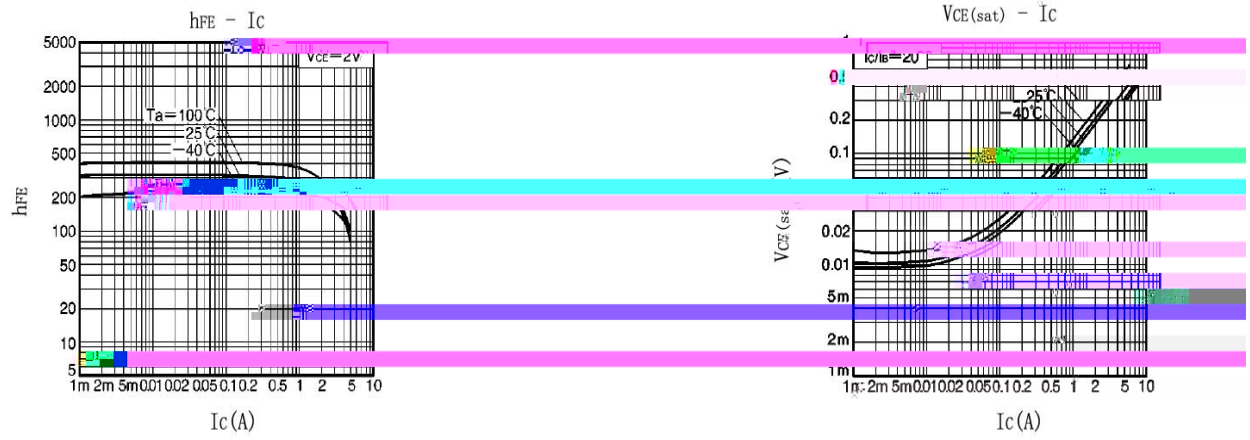
v ̈Ω Parameter	٩ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	3.0	A
Peak Collector Current - Continuous	I_{CM}	5.0	A
Collector Power Dissipation	P_C	0.4	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

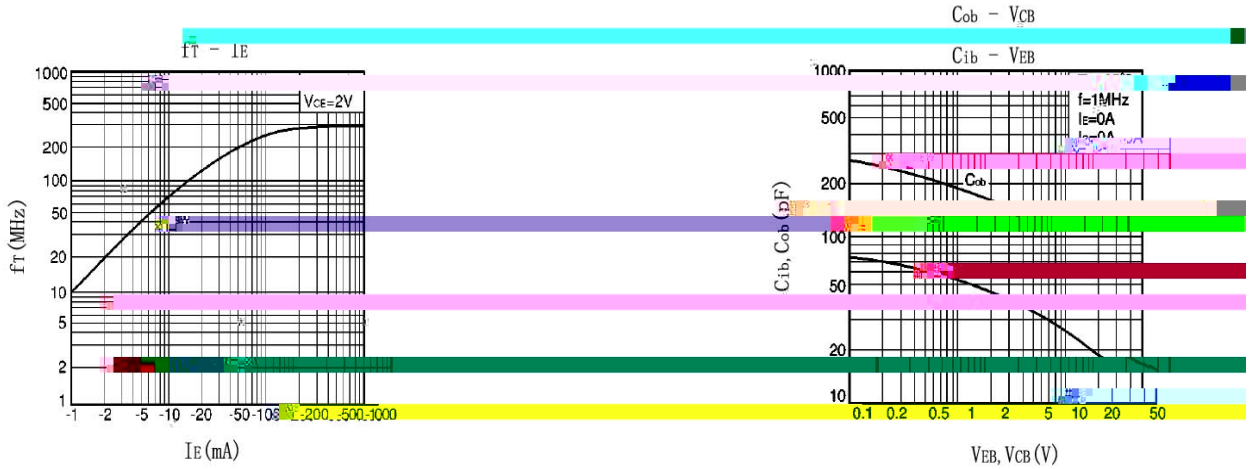
/ Electrical Characteristics(Ta=25)

v ̈Ω Parameter	٩ N Symbol	‼ ;ˆ Ţ Test Conditions	ώ ṇ Ö Min	Ɛ ʒ Ö Typ	ώ ᶻ Ö Max	D Ч Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=50μA I_E=0	40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	20			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=50μA I_C=0	6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=30V I_E=0			0.1	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	μA
DC Current Gain	h_{FE}	V_{CE}=2.0V I_C=0.1A	120		560	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=2.0A I_B=0.1A		0.2	0.5	V
Transition Frequency	f_T	V_{CE}=2.0V I_C=0.5A f=100MHz		290		MHz
Output Capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz		25		pF

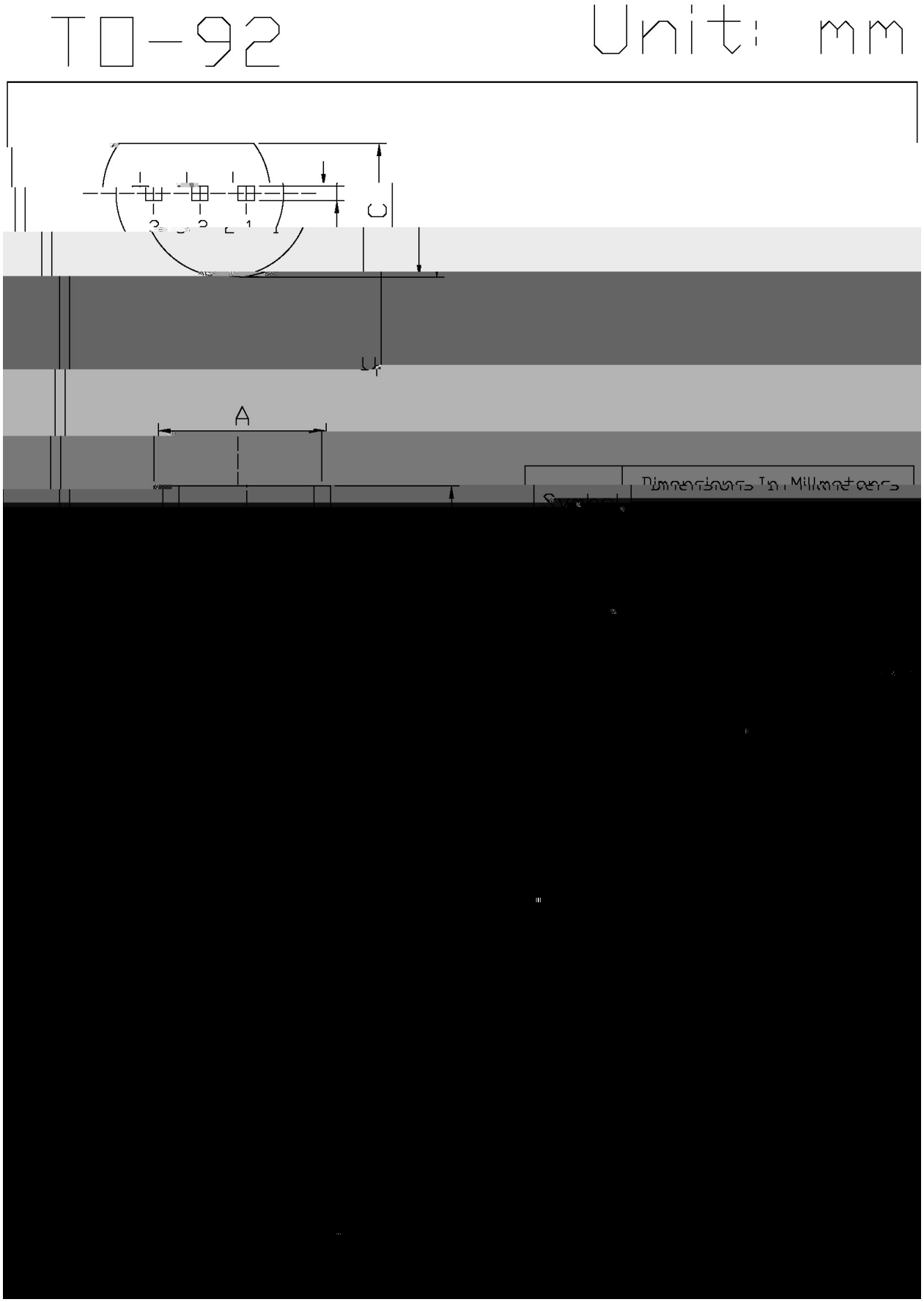
/ Electrical Characteristic Curve







/ Package Dimensions



( ) / Temperature Profile for Dip Soldering(Pb-Free)

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Note: